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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(use as many sheets as necessary)

**COMPLETE IF KNOWN**

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Confirmation Number 1242  
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First Named Inventor Ritzdorf  
Group Art Unit 2823  
Examiner Name Deven M. Collins

Attorney Docket No. 29195.8162US

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**U.S. PATENT DOCUMENTS**

EXAMINER INITIALS	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		NUMBER	Kind Code (if known)			
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**FOREIGN PATENT DOCUMENTS**

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		Office	Number	Kind Code (if known)				

**OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS**

EXAMINER INITIALS	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume/issue number(s), publisher, city and/or country where published.
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	AL	DUBIN, V.M., SHACHAM-DIAMAND, Y., ZHAO, B., VASUDEVA, P.K. and TING, C.H., "Sub-Half Micron Electroless Cu Metallization," Materials Research Society Symposium Proceedings, Vol. 427, San Francisco (1996).
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